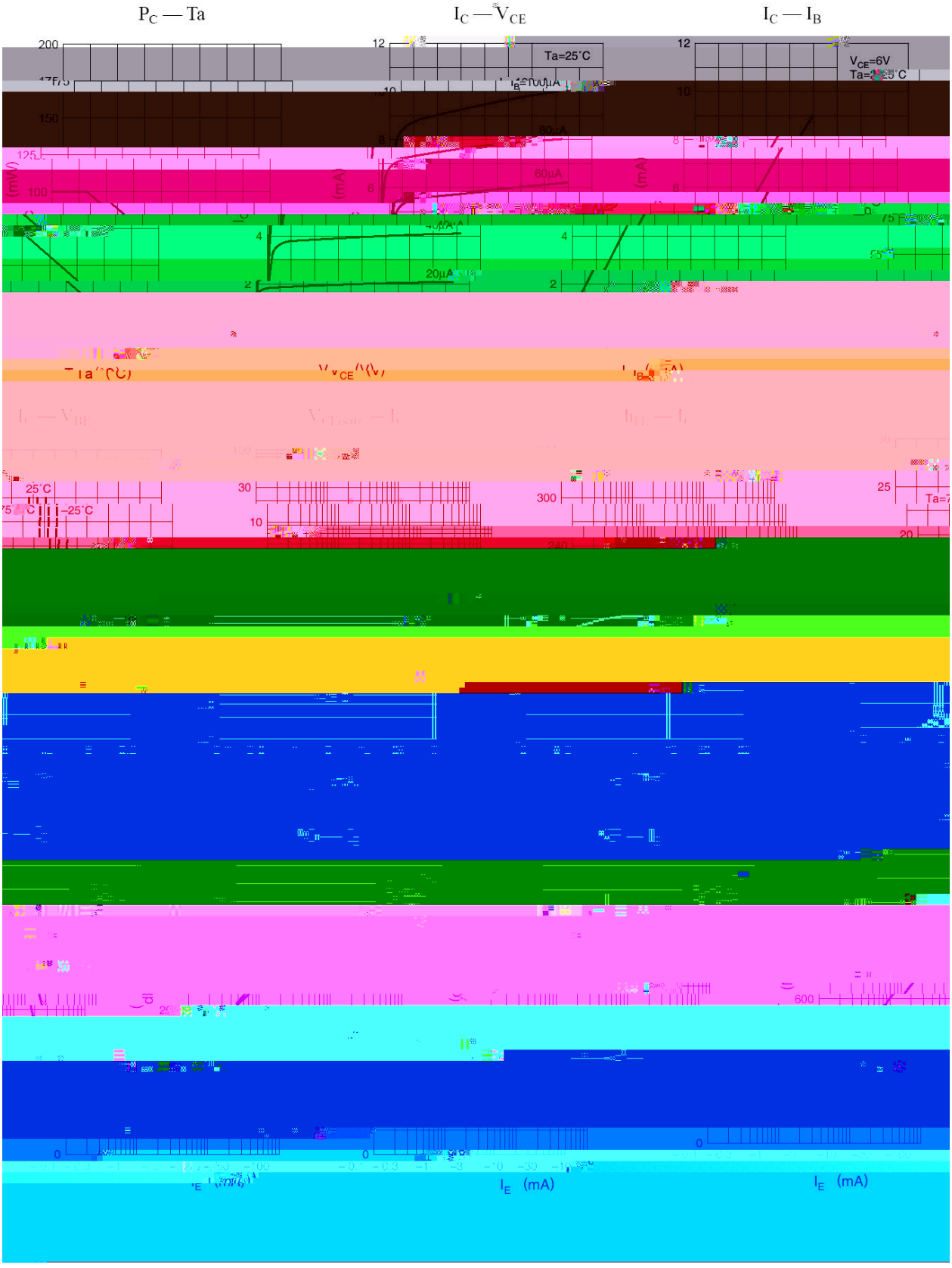
## / Absolute Maximum Ratings(Ta=25 )

| v Ѽ<br>Parameter | ч N<br>Symbol | Ѽ Ө<br>Rating | D Ч<br>Unit |
|---|---|---|---|
| Collector to Base Voltage | $V_{CBO}$ | 30 | V |
| Collector to Emitter Voltage | $V_{CEO}$ | 20 | V |
| Emitter to Base Voltage | $V_{EBO}$ | 3.0 | V |
| Collector Current | $I_C$ | 15 | mA |
| Collector Power Dissipation | $P_C$ | 100 | mW |
| Junction Temperature | $T_j$ | 150 | |
| Storage Temperature Range | $T_{stg}$ | -55 150 | |

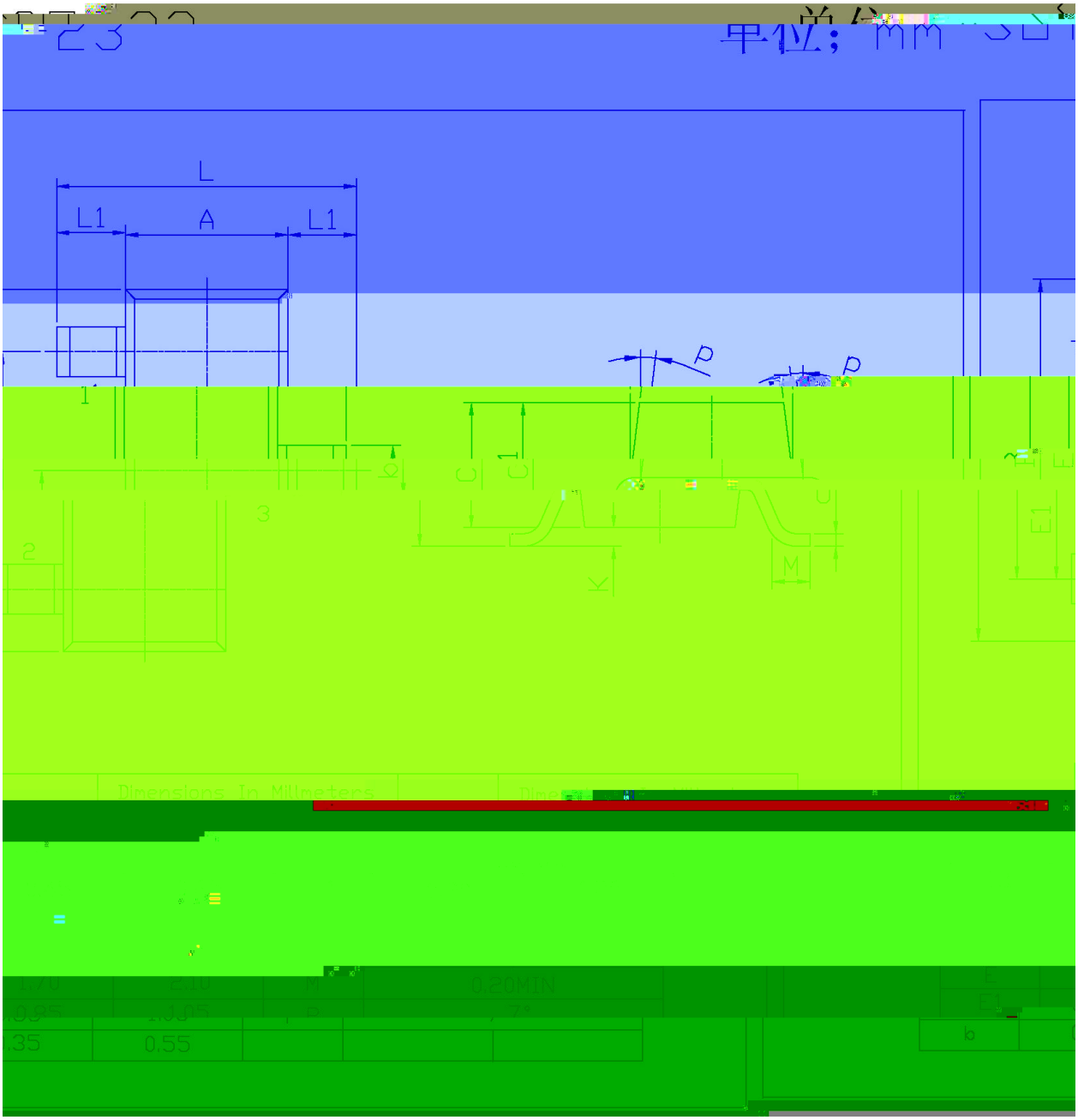
## / Electrical Characteristics(Ta=25 )

| v Ѽ<br>Parameter | ч N<br>Symbol | Ш :ϯ Ţ<br>Test Conditions | ѡ ṇ Ө<br>Min | Ɛ ʒ Ө<br>Typ | ѡ ᶻ Ө<br>Max | D Ч<br>Unit |
|---|---|---|---|---|---|---|
| Collector- Base Breakdown Voltage | $V_{CBO}$ | $I_C$=10μA | 30 | | | V |
| Emitter-Base Breakdown Voltage | $V_{EBO}$ | $I_E$=10μA | 3.0 | | | V |
| DC Current Gain | $h_{FE}$ | $V_{CE}$=6.0V $I_c$=1.0mA | 40 | | 260 | |
| Transition Frequency | $f_T$ | $V_{CB}$=6.0V $I_c$=1.0mA | 450 | 650 | | MHz |
| Base to Emitter Voltage | $V_{BE}$ | $V_{CB}$=6.0V $I_c$=1.0mA | | 0.72 | | V |
| Common Emitter Reverse Transfer Capacitance | $C_{re}$ | $V_{CB}$=6.0V $I_C$=1.0mA f=10.7MHz | | 0.8 | 1.0 | PF |
| Power Gain | $P_G$ | $V_{CB}$=6.0V $I_C$=1.0mA f=100MHz | | 24 | | dB |
| Noise Figure | NF | $V_{CB}$=6.0V $I_C$=1.0mA f=100MHz | | 3.3 | | dB |

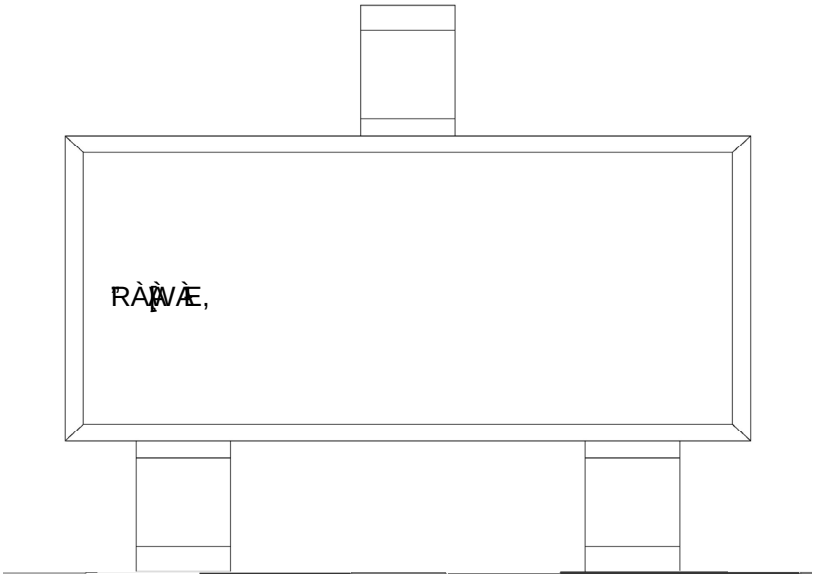
## / Electrical Characteristic Curve



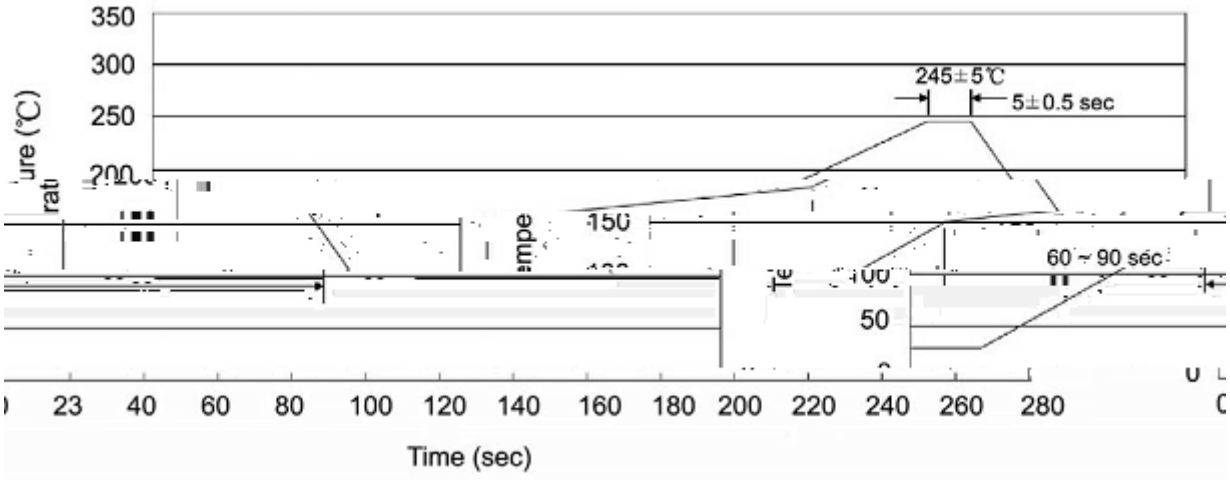
## / Package Dimensions



## / Marking Instructions



## ( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)




ب ˝ χ

1 Ĺ ♬ □ ỷ 25 Ḱ 150 ł ı ˋH ڑ 60 Ḱ 90sec;

2 Š Ë □ ỷ 245 ° 5 ł ı ˋH ڑ ˋY ﾊ ㎞ 5 ° 0.5sec;

3 ì ˙ ﾘ ˛ ↄ ෯ ỷ ㎞ 2 Ḱ 10 ł /sec.

Note:

1.Preheating:25~150 ł , Time:60~90sec.

2.Peak Temp.:245 ° 5 ł , Duration:5 ° 0.5sec.

3.